

CGD1042H

1 GHz, 23 dB gain high output power doubler

Rev. 01 — 9 October 2007

Product data sheet

1. Product profile

1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V Direct Current (DC), employing Hetero junction Field Effect Transistor (HFET) GaAs dies.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- High output power capability
- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Rugged construction
- Unconditionally stable
- Thermal optimized design

1.3 Applications

■ CATV systems operating in the 40 MHz to 1000 MHz frequency range

1.4 Quick reference data

Table 1. Quick reference data

Bandwidth to 1000 MHz; $V_B = 24 \text{ V (DC)}$; $T_{mb} = 35 \,^{\circ}\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	f = 45 MHz	- 1	21.5	1. 1.	dB
		f = 1000 MHz	22.0	23.0	24.0	dB
I _{tot}	total current		<u>[1]</u> 430	450	470	mA

^[1] Direct Current (DC).





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2. Pinning information

Table 2. Pinning

	•	
Pin	Description	Simplified outline Symbol
1	input	
2, 3	common	1 3 5 7 9
5	+V _B	
7, 8	common	12/3/7/8
9	output	sym095

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
CGD1042H	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{B}	supply voltage		-	30	V
$V_{i(RF)}$	RF input voltage	single tone	-	75	dBmV
T _{stg}	storage temperature		-40	+100	°C
T _{mb}	mounting base temperature		-20	+100	°C

1 GHz, 23 dB gain high output power doubler

5. Characteristics

Table 5. Characteristics

Bandwidth to 1000 MHz; $V_B = 24 \text{ V (DC)}$; $T_{mb} = 35 \,^{\circ}\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 45 MHz		-	21.5	-	dB
		f = 1000 MHz		22.0	23.0	24.0	dB
SL _{sl}	slope straight line	f = 45 MHz to 1000 MHz	[1]	-	1.5	-	dB
FL	flatness of frequency response	f = 45 MHz to 1000 MHz	[2]	-	0.5	-	dB
СТВ	composite triple beat	$V_0 = 55 \text{ dBmV at } 1000 \text{ MHz}$	[3]	-	-83	-	dBc
		$V_0 = 59 \text{ dBmV at } 1000 \text{ MHz}$	[3]	-	-75	-70	dBc
CSO	composite second-order distortion	$V_0 = 55 \text{ dBmV}$ at 1000 MHz	[3]	-	-80	-	dBc
		$V_0 = 59 \text{ dBmV at } 1000 \text{ MHz}$	[3]	-	-76	-68	dBc
Xmod	cross modulation	$V_0 = 55 \text{ dBmV at } 1000 \text{ MHz}$	[3]	-	-75	-	dBc
		$V_0 = 59 \text{ dBmV at } 1000 \text{ MHz}$	[3]	-	-67	-	dBc
CCN	carrier-to-composite noise	$V_0 = 55 \text{ dBmV at } 1000 \text{ MHz}$	[3]	-	65	-	dBc
		$V_0 = 59 \text{ dBmV at } 1000 \text{ MHz}$	[3]	55	58	-	dBc
RL _{in} inp	input return loss	f = 45 MHz to 200 MHz		20.0	-	-	dB
		f = 200 MHz to 550 MHz		17.5	-	-	dB
		f = 550 MHz to 870 MHz		15.0	-	-	dB
		f = 870 MHz to 914 MHz		14.5	-	-	dB
		f = 914 MHz to 1000 MHz		14.0	-	-	dB
RL_out	output return loss	f = 45 MHz to 200 MHz		21.0	-	-	dB
		f = 200 MHz to 550 MHz		20.0	-	-	dB
		f = 550 MHz to 870 MHz		18.0	-	-	dB
		f = 870 MHz to 914 MHz		17.5	-	-	dB
		f = 914 MHz to 1000 MHz		17.0	-	-	dB
NF	noise figure	f = 50 MHz to 1000 MHz		-	5.0	5.5	dB
I _{tot}	total current		<u>[4]</u>	430	450	470	mΑ

^[1] G_p at 1000 MHz minus G_p at 45 MHz.

^[2] flatness straight line (peak to valley).

^{[3] 79} NTSC channels + 75 digital channels (-6 dB offset); tilt extrapolated to 18 dB at 1000 MHz.

^[4] Direct Current (DC).

1 GHz, 23 dB gain high output power doubler

6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

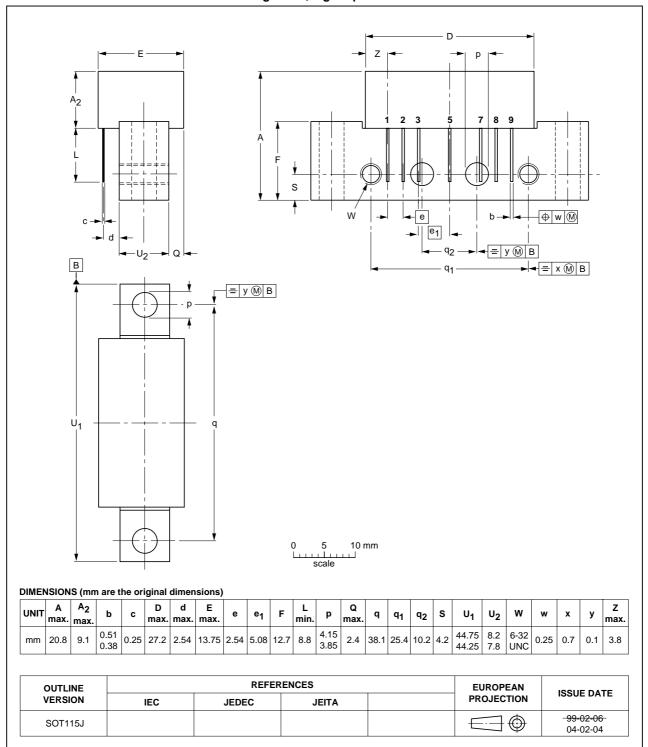


Fig 1. Package outline SOT115J

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7. Abbreviations

Table 6. Abbreviations

Acronym	Description
CATV	Community Antenna TeleVision
NTSC	National Television Standard Committee
RF	Radio Frequency
UNC	UNified Coarse

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD1042H_1	20071009	Product data sheet	-	-

1 GHz, 23 dB gain high output power doubler

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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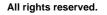
1 GHz, 23 dB gain high output power doubler

11. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data
2	Pinning information 2
3	Ordering information
4	Limiting values 2
5	Characteristics 3
6	Package outline 4
7	Abbreviations 5
8	Revision history 5
9	Legal information 6
9.1	Data sheet status 6
9.2	Definitions
9.3	Disclaimers 6
9.4	Trademarks6
10	Contact information 6
11	Contents 7

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